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## (54) RESIST PATTERN FORMING MATERIAL

(57)Abstract:

**PROBLEM TO BE SOLVED:** To provide a resist pattern forming material capable of giving a high resolution resist pattern adaptable to a fine pattern which is required when a semiconductor device is manufactured by a via first dual damascene method and producing no resist residue.

**SOLUTION:** In the resist pattern forming material obtained by disposing a coating layer of a chemical amplification type positive type resist composition containing (A) a polyhydroxystyrene having acid dissociable dissolution inhibiting groups substituted for at least part of the hydrogen atoms of hydroxyl groups and (B) a compound which generates an acid when irradiated with radiation on a substrate on which a first interlayer insulation layer, an etching stopper layer and a second interlayer insulation layer have been stacked in order, the component (A) has  $\leq 40\%$  remaining rate of the acid dissociable dissolution inhibiting groups after a dissociation test with hydrochloric acid.

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